



6-Pin DIP Optoisolator Transistor Output

The MOC8100 device consists of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector. It is designed for applications requiring higher output collector current (I_C) with lower input drive current (I_F).

- Current Transfer Ratio Guaranteed to be > 50% at 1 mA LED Drive Level
- **To order devices that are tested and marked per VDE 0884 requirements, the suffix "V" must be included at end of part number. VDE 0884 is a test option.**

Applications

- Appliances, Measuring Instruments
- General Purpose Switching Circuits
- Programmable Controllers
- Portable Electronics
- Interfacing and coupling systems of different potentials and impedances
- Low Power Logic Circuits
- Telecommunications Equipment

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
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INPUT LED

Reverse Voltage	V_R	6	Volts
Forward Current — Continuous	I_F	60	mA
LED Power Dissipation @ $T_A = 25^\circ\text{C}$ with Negligible Power in Output Detector Derate above 25°C	P_D	120 1.41	mW mW/°C

OUTPUT TRANSISTOR

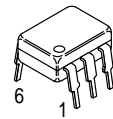
Collector–Emitter Voltage	V_{CEO}	30	Volts
Emitter–Base Voltage	V_{EBO}	7	Volts
Collector–Base Voltage	V_{CBO}	70	Volts
Collector Current — Continuous	I_C	150	mA
Detector Power Dissipation @ $T_A = 25^\circ\text{C}$ with Negligible Power in Input LED Derate above 25°C	P_D	150 1.76	mW mW/°C

TOTAL DEVICE

Isolation Surge Voltage ⁽¹⁾ (Peak ac Voltage, 60 Hz, 1 sec Duration)	V_{ISO}	7500	Vac(pk)
Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	250 2.94	mW mW/°C
Ambient Operating Temperature Rang	T_A	-55 to +100	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C
Soldering Temperature (10 sec, 1/16" from case)	T_L	260	°C

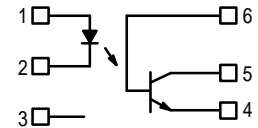
1. Isolation surge voltage is an internal device dielectric breakdown rating.
For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

MOC8100



STANDARD THRU HOLE

SCHEMATIC



- PIN 1. LED ANODE
2. LED CATHODE
3. N.C.
4. EMITTER
5. COLLECTOR
6. BASE

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)⁽¹⁾

Characteristic	Symbol	Min	Typ ⁽¹⁾	Max	Unit	
INPUT LED						
Forward Voltage ($I_F = 10\text{ mA}$)	V_F	—	$T_A = 0\text{--}70^\circ\text{C}$	1.15	1.4	Volts
			$T_A = -55^\circ\text{C}$	1.3	—	
			$T_A = 100^\circ\text{C}$	1.05	—	
Reverse Leakage Current ($V_R = 6\text{ V}$)	I_R	—	0.05	10	μA	
Capacitance ($V = 0\text{ V}$, $f = 1\text{ MHz}$)	C_J	—	18	—	pF	

OUTPUT TRANSISTOR

Collector–Emitter Dark Current ($V_{CE} = 5\text{ V}$, $T_A = 25^\circ\text{C}$) ($V_{CB} = 30\text{ V}$, $T_A = 70^\circ\text{C}$)	I_{CEO}	—	3	25	nA
	I_{CEO}	—	0.05	50	μA
Collector–Base Dark Current ($V_{CB} = 5\text{ V}$)	I_{CBO}	—	0.2	10	nA
Collector–Emitter Breakdown Voltage ($I_C = 1\text{ mA}$)	$V_{(BR)CEO}$	30	45	—	Volts
Collector–Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{A}$)	$V_{(BR)CBO}$	70	100	—	Volts
Emitter–Base Breakdown Voltage ($I_E = 100\text{ }\mu\text{A}$)	$V_{(BR)EBO}$	7	7.8	—	Volts
DC Current Gain ($I_C = 1\text{ mA}$, $V_{CE} = 5\text{ V}$) (Typical Value)	h_{FE}	—	600	—	—
Collector–Emitter Capacitance ($f = 1\text{ MHz}$, $V_{CE} = 0$)	C_{CE}	—	7	—	pF
Collector–Base Capacitance ($f = 1\text{ MHz}$, $V_{CB} = 0$)	C_{CB}	—	19	—	pF
Emitter–Base Capacitance ($f = 1\text{ MHz}$, $V_{EB} = 0$)	C_{EB}	—	9	—	pF

COUPLED

Output Collector Current ($I_F = 1\text{ mA}$, $V_{CE} = 5\text{ V}$) ($I_F = 1\text{ mA}$, $V_{CE} = 5\text{ V}$, $T_A = 0\text{ to }+70^\circ\text{C}$)	$I_C\text{ (CTR)}^{(2)}$	0.5 (50)	1 (100)	—	mA (%)
		0.3 (30)	0.6 (60)	—	
Collector–Emitter Saturation Voltage ($I_C = 100\text{ }\mu\text{A}$, $I_F = 1\text{ mA}$)	$V_{CE(sat)}$	—	0.22	0.5	Volts
Turn–On Time ($I_C = 2\text{ mA}$, $V_{CC} = 10\text{ V}$, $R_L = 100\text{ }\Omega$) ⁽³⁾	t_{on}	—	9	20	μs
Turn–Off Time ($I_C = 2\text{ mA}$, $V_{CC} = 10\text{ V}$, $R_L = 100\text{ }\Omega$) ⁽³⁾	t_{off}	—	7	20	μs
Rise Time ($I_C = 2\text{ mA}$, $V_{CC} = 10\text{ V}$, $R_L = 100\text{ }\Omega$) ⁽³⁾	t_r	—	3.8	—	μs
Fall Time ($I_C = 2\text{ mA}$, $V_{CC} = 10\text{ V}$, $R_L = 100\text{ }\Omega$) ⁽³⁾	t_f	—	5.6	—	μs
Isolation Voltage ($f = 60\text{ Hz}$, $t = 1\text{ sec}$) ⁽⁴⁾	V_{ISO}	7500	—	—	Vac(pk)
Isolation Resistance ($V = 500\text{ V}$) ⁽⁴⁾	R_{ISO}	10^{11}	—	—	Ω
Isolation Capacitance ($V = 0\text{ V}$, $f = 1\text{ MHz}$) ⁽⁴⁾	C_{ISO}	—	0.2	2	pF

1. Always design to the specified minimum/maximum electrical limits (where applicable).
2. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.
3. For test circuit setup and waveforms, refer to Figure 11.
4. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

TYPICAL CHARACTERISTICS

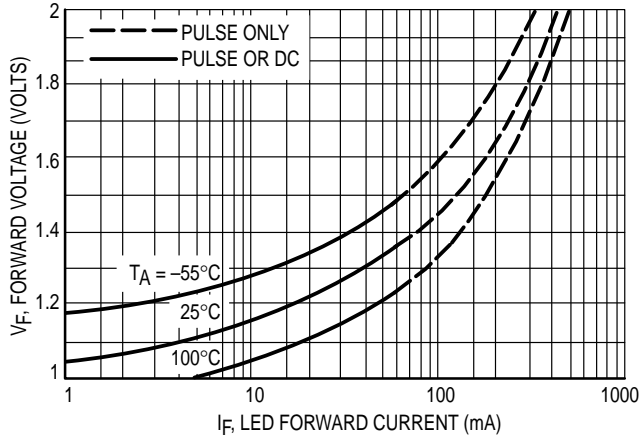


Figure 1. LED Forward Voltage versus Forward Current

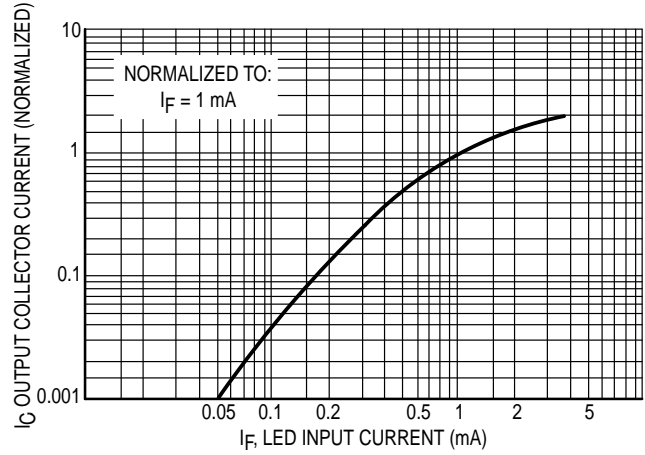


Figure 2. Output Current versus Input Current

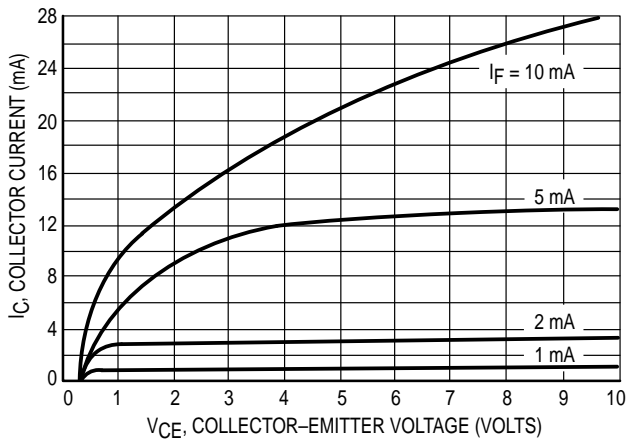


Figure 3. Collector Current versus Collector-Emitter Voltage

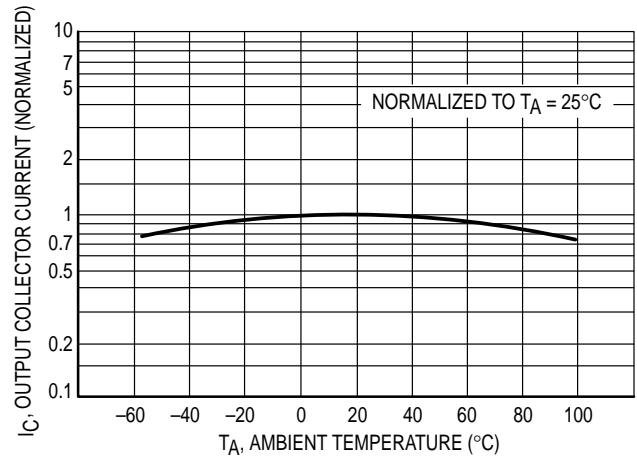


Figure 4. Output Current versus Ambient Temperature

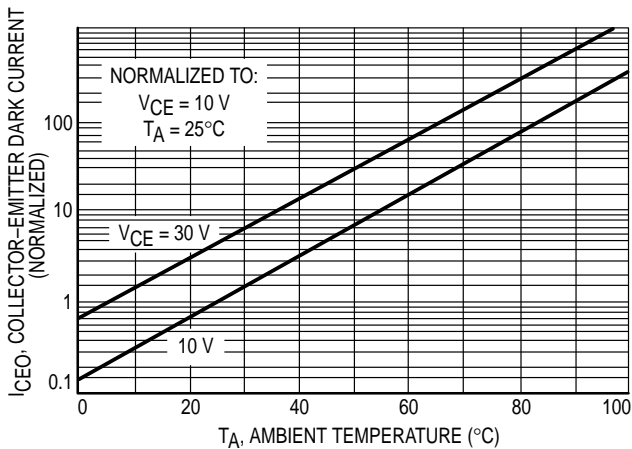


Figure 5. Dark Current versus Ambient Temperature

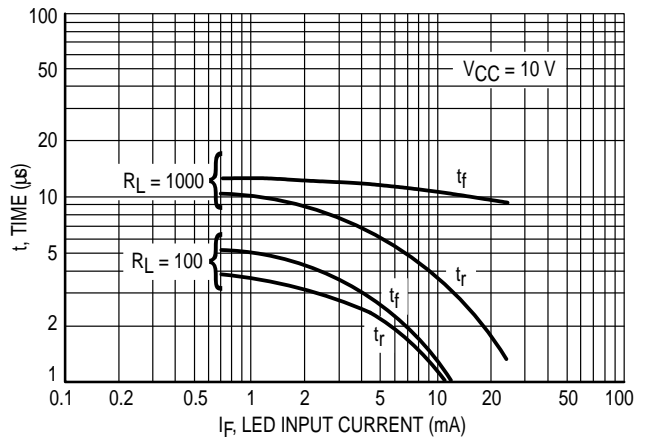


Figure 6. Rise and Fall Times (Typical Values)

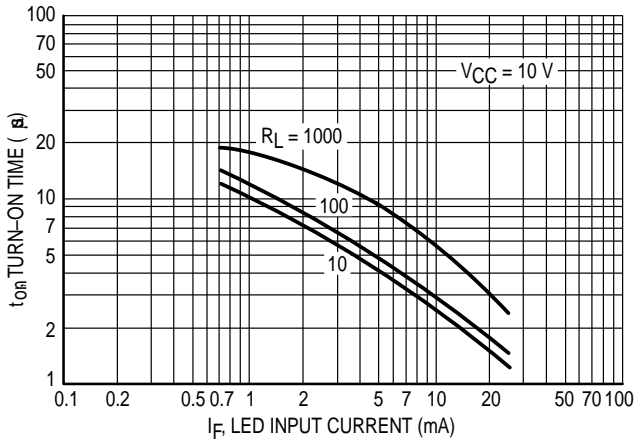


Figure 7. Turn-On Switching Times

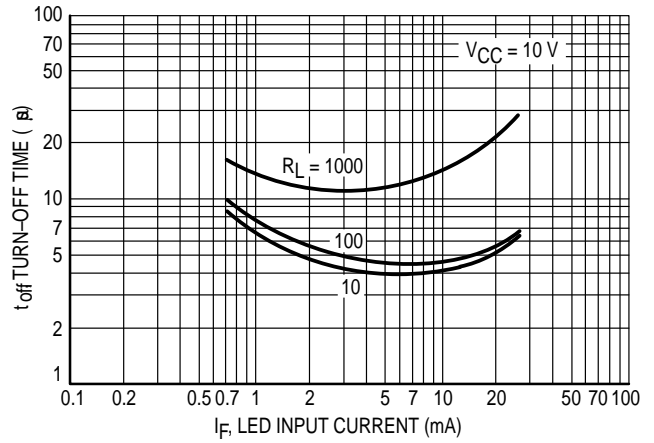


Figure 8. Turn-Off Switching Times

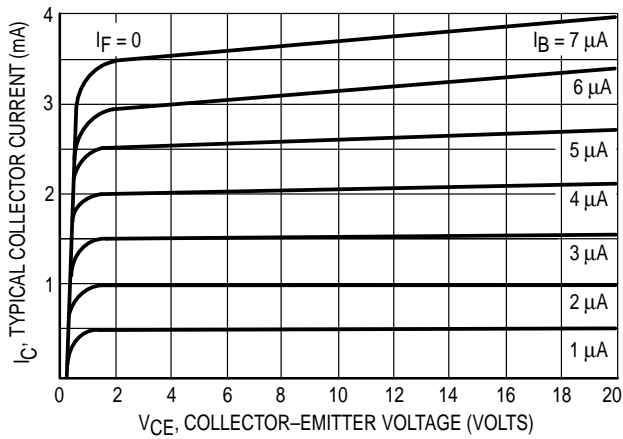


Figure 9. DC Current Gain (Detector Only)

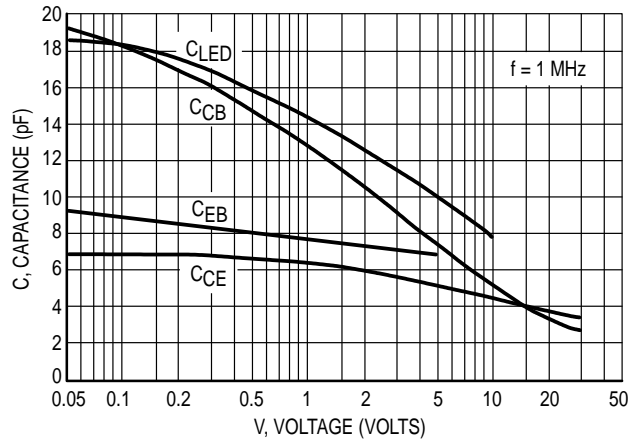


Figure 10. Capacitances versus Voltage

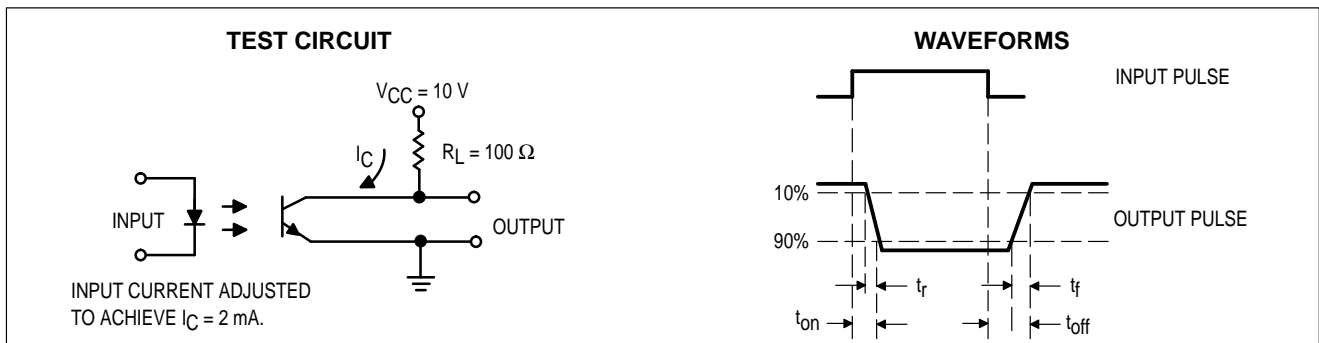
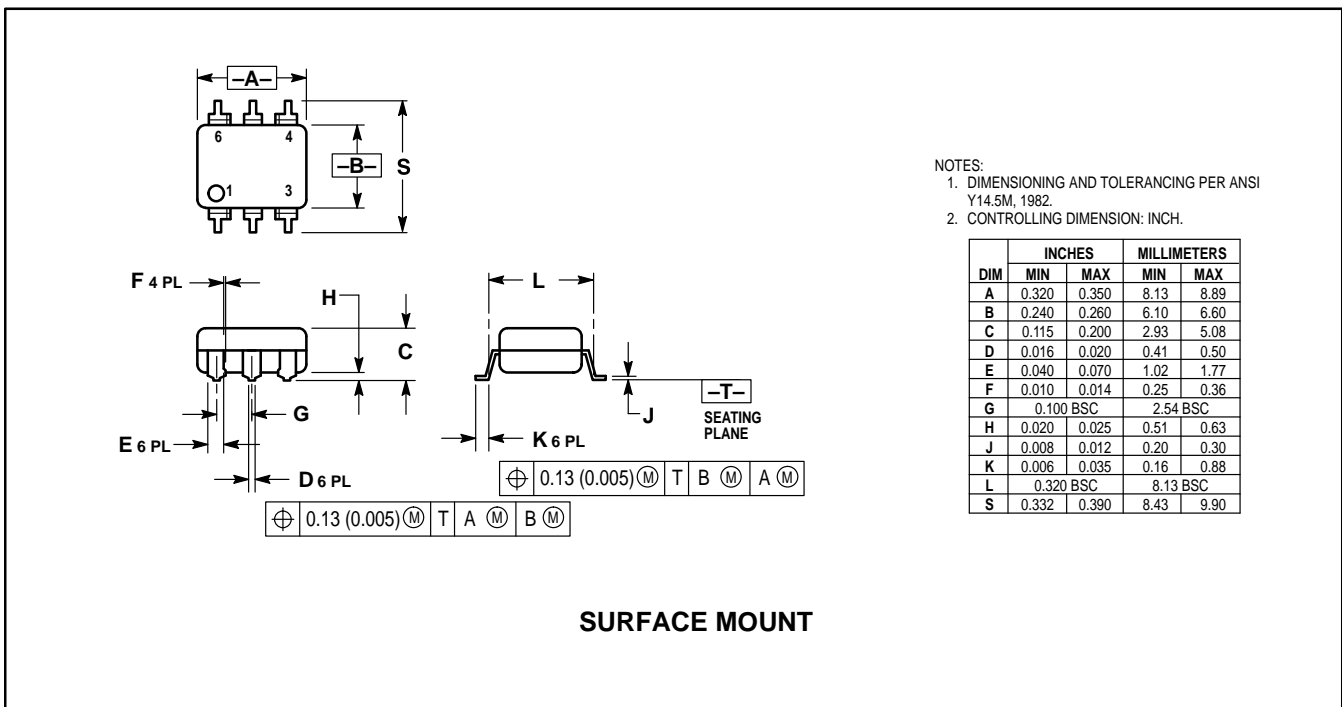
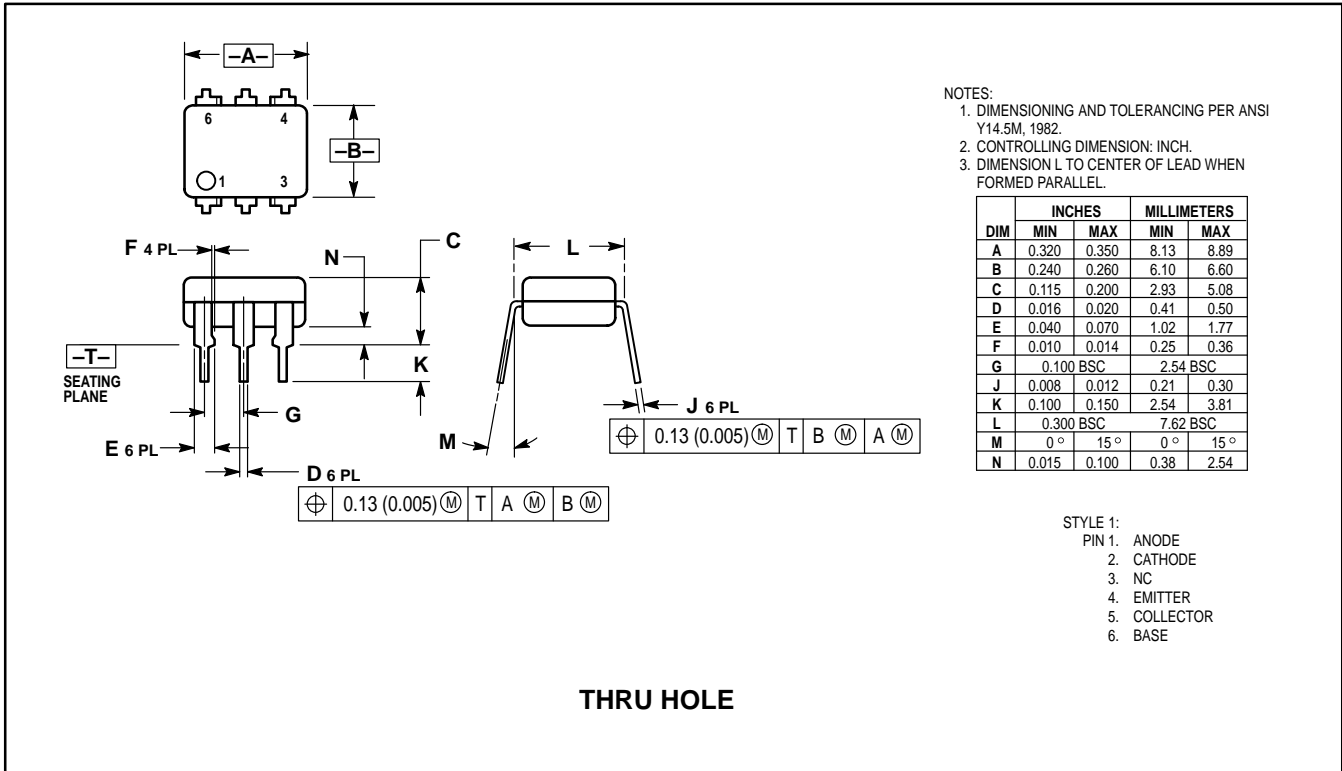
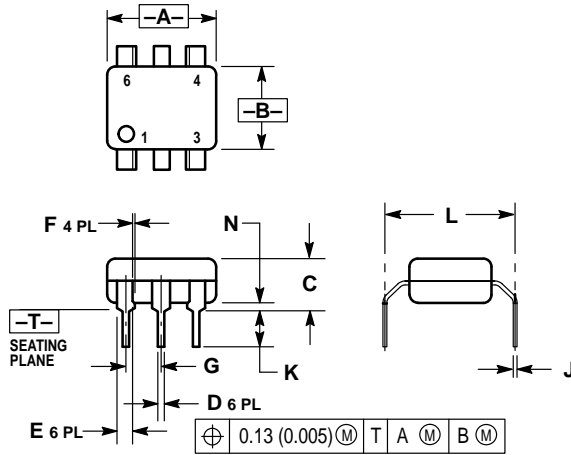


Figure 11. Switching Time Test Circuit and Waveforms

PACKAGE DIMENSIONS





- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.320	0.350	8.13	8.89
B	0.240	0.260	6.10	6.60
C	0.115	0.200	2.93	5.08
D	0.016	0.020	0.41	0.50
E	0.040	0.070	1.02	1.77
F	0.010	0.014	0.25	0.36
G	0.100 BSC		2.54 BSC	
J	0.008	0.012	0.21	0.30
K	0.100	0.150	2.54	3.81
L	0.400	0.425	10.16	10.80
N	0.015	0.040	0.38	1.02

0.4" LEAD SPACING

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